

A 150MHz Superscalar RISC Processor with Pseudo Vector Processing Feature

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Presentation Outline

- Design Goals
- Pseudo Vector Processing Feature
- Processor Overview
- Performance
- Physical Characteristics
- Summary

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Design Goals

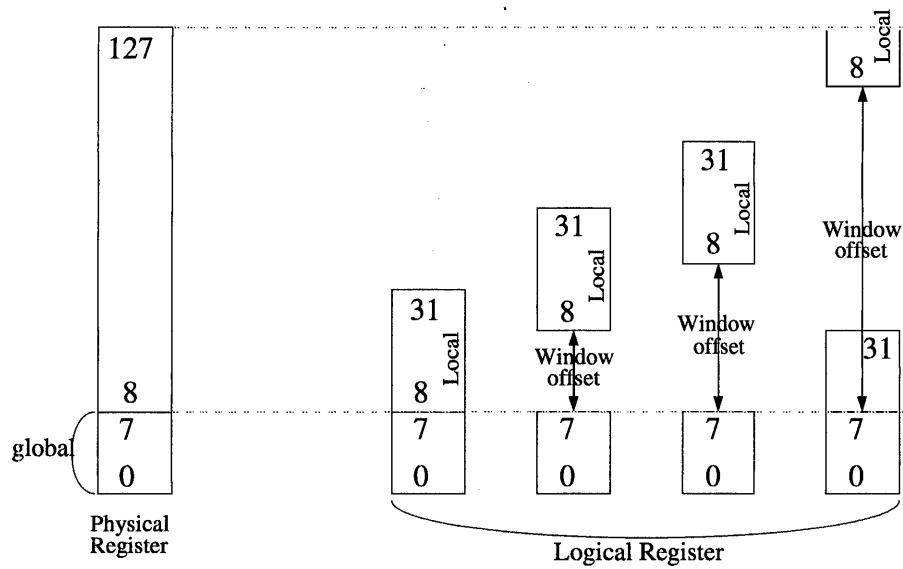
- Competitive Performance
- Implementation of Pseudo Vector Processing Feature
- Effective High Memory Throughput
- 0.3 μ m CMOS Technology
- High Operating Frequency
- Low Power

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Architectural Features

- Support for Uncacheable Memory Pages
- Pseudo Vector Processing Feature based on Slide-Window Registers (PVP-SW)
 - Utilize Software-Pipelining Technique
 - Flexible Software-Supported Register Renaming
- Architectural Extensions
 - Slide-Windowed Floating-Point Registers
 - Preload Instruction
 - Poststore Instruction

Slide-Windowed Floating-Point Registers



global registers - - - 8 or 12 or 16

Window offset = FWSTP (Floating Window Start Pointer)

FWSTPset instruction

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Preload Instruction

- Directly specify 128 Physical FPRs
 - to hide Memory Access Latency
 - 7-bit register number
- Data Transfer from Main Memory to FPR directly
 - No Cache Pollution
- Preload 8B Data / cycle
 - 1.2GB/s Peak Transfer Rate @ 150MHz
- Compatibility with Cache

1st cache	2nd cache	Action
hit	don't care	1st cache -> FPR
miss	don't care	M.M. -> FPR

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Poststore Instruction

- Directly specify 128 Physical FPRs
 - to hide FP Latency
 - 7-bit register number
- Compatibility with Cache
 - 1st or 2nd cache hit -> Cache Store and M.M. Store
 - 1st and 2nd cache miss -> M.M. Store only

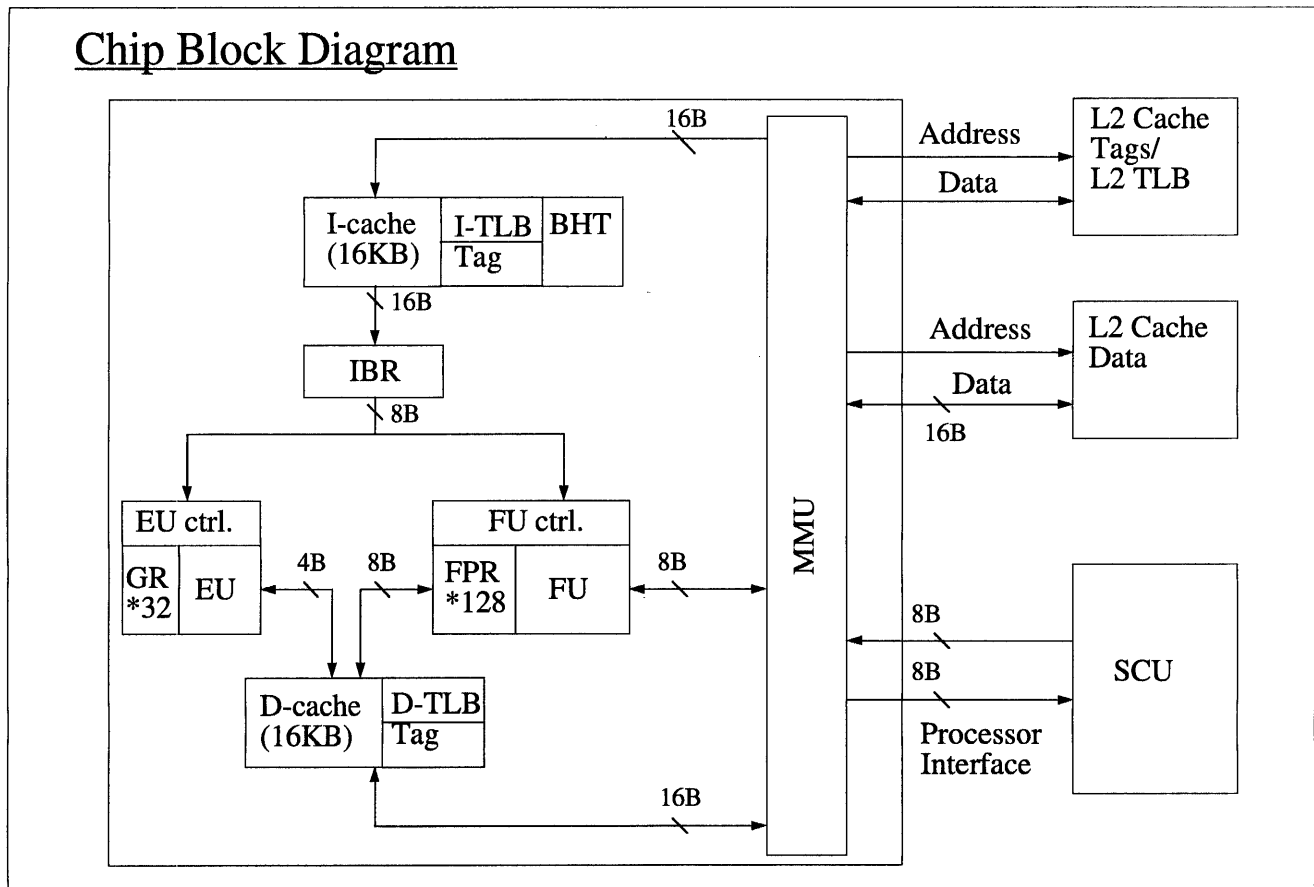
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Processor Core Features

- Superscalar with 2 Instruction Issues
- Up to 4 Operations / cycle
- 2 Integer ALUs, 2 SMUs(Shift Merge Unit)
- 2 Floating-point Operations(FMPADD) / cycle
- Branch History Table with 2-bit x 1024 Entries

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Hot Chips VII

Chip Block Diagram



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TLB Organization

• 1st Level TLB

I-TLB 256 Entries direct mapped
 6 Block Table Entries 512K-32MB/Entry
 1 Anti-Thrashing Entry

D-TLB 256 Entries direct mapped
 6 Block Table Entries 512K-32MB/Entry
 1 Anti-Thrashing Entry

• 2nd Level TLB

I-TLB 1K-4K Entries 2 way set associative

D-TLB 1K-4K Entries 2 way set associative

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Cache Organization

• 1st Level Cache

I-Cache 16KB
 D-Cache 16KB
 Direct Mapped , 32B / Block
 Single Bit Error Detection Parity

• 2nd Level Cache

I/D Combined 512KB-8MB
 Direct Mapped , 128B / Line
 Single Bit Error Correction, Double bits Error
 Detection ECC / 4B

• Cache Miss Optimization

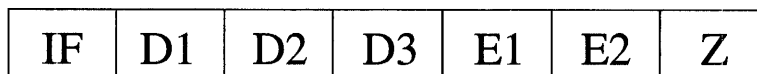
-Hit under Miss
 -Pipelined Instruction Prefetching (up to 4)

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Integer Pipeline : 6 stages

Bypass ←←←←←

IF : Instruction Fetch
 D : Decode
 E : Execution
 A : Cache/TLB Access
 N : Nullification / Interruption
 W : GR Write

Floating Pipeline : 7 stages

Bypass ←

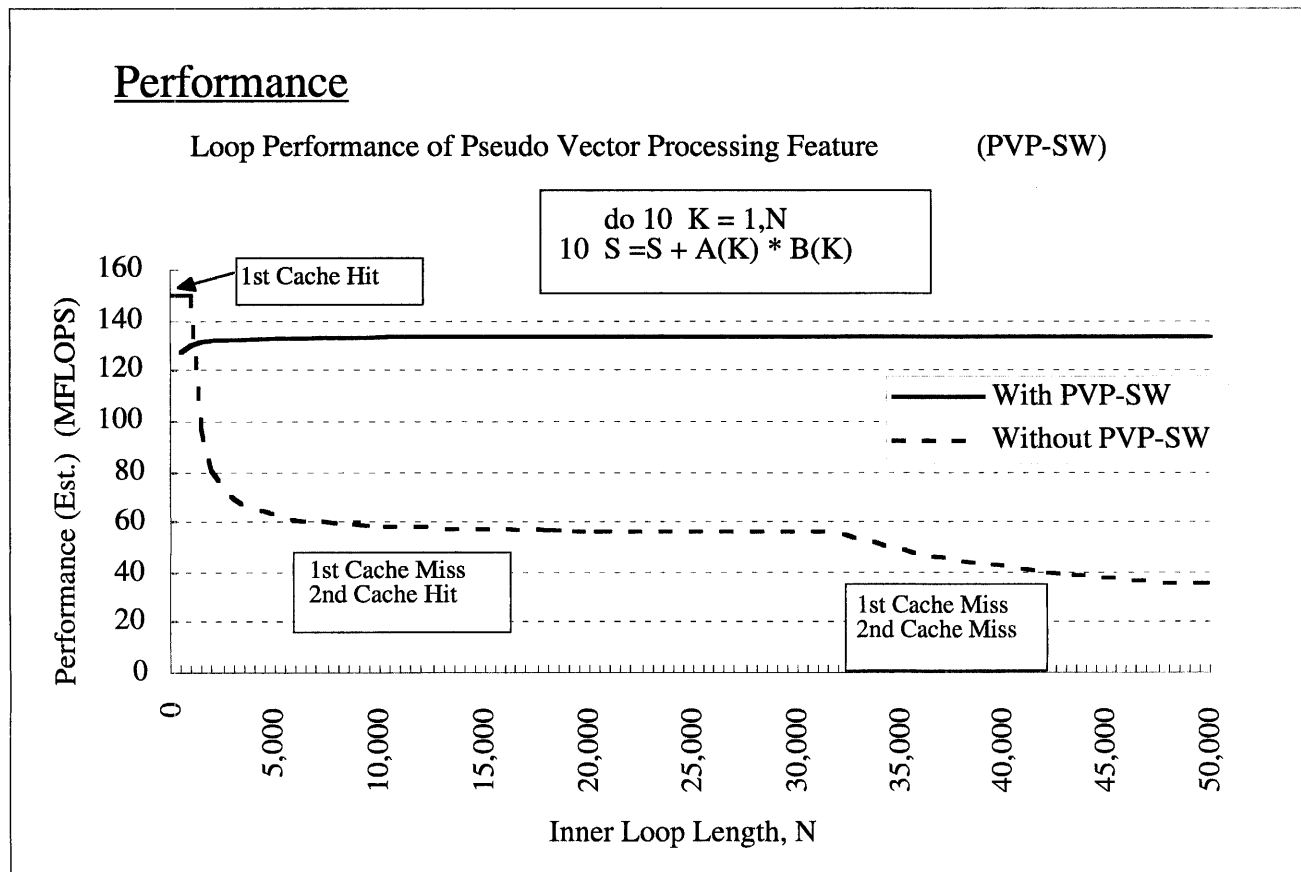
D1 : FPR Number Conversion
 D2 : Dependency Check
 D3 : Source Operand Read
 E1 : Execution 1
 E2 : Execution 2
 Z : FPR Write

FP Latency and Issue Rate

	Single Precision	Double Precision
	Latency / Issue Rate	Latency / Issue Rate
Add, Sub	2 / 1	2 / 1
Multiply	2 / 1	2 / 1
FMPYADD, FMPYSUB	2 / 1	2 / 1
Divide	10 / 9	17 / 16
Square Root	16 / 15	30 / 29

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Physical Characteristics

Process Technology	0.3 μm CMOS
Cycle Time	150 MHz (*1) > 200 MHz (*2)
Die Size	15.7 mm x 15.7 mm
Number of Transistors	4.5 M
Package	1672 pin CCB (C4) , 520 signals
Power Supply	2.5 V
Power Dissipation	13 W @ 150 MHz
Peak MFLOPS / W	23 MFLOPS / W

(*1) Worst Silicon Processing and Worst Environment

(*2) Typical Silicon Processing and Worst Environment

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Device Characteristics

• CMOS Circuit

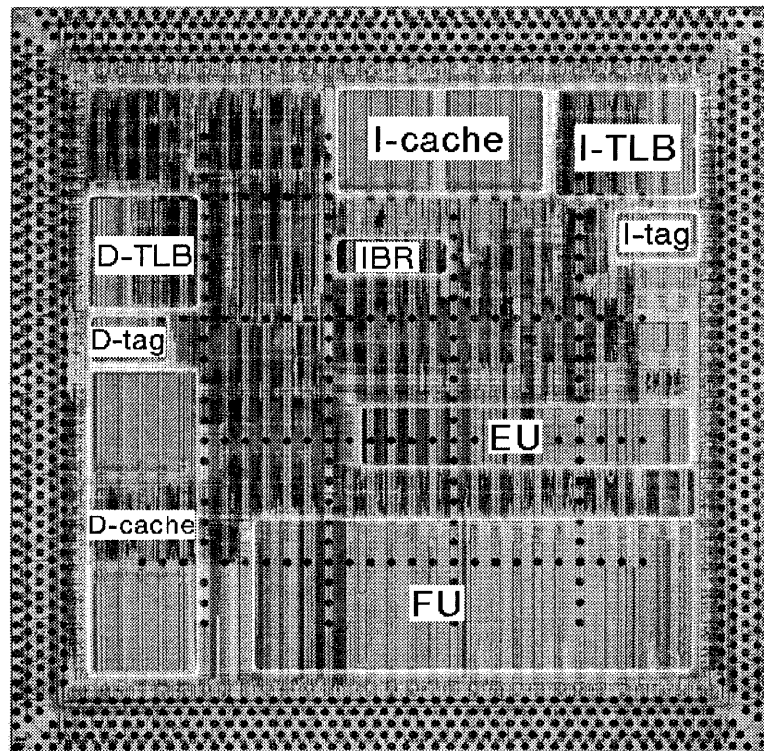
Ldrawn	0.3 μm
L _{eff}	0.25 μm
T _{ox}	6.5 nm

• Interconnection

Layers 4 Metal layers

	Width (μm)	Thickness (μm)	Pitch (μm)		
			Uncontacted	Contacted	Design Rule
AL1	0.5	0.65	1.0	1.4	1.4
AL2	0.5	0.65	1.0	1.4	1.4
AL3	1.4	1.15	1.8	2.4	2.8
AL4	1.4	1.45	2.8	2.8	2.8

Chip Photograph



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Summary

- High Performance Superscalar RISC Processor
- PVP-SW Feature Support
- Optimized to Large Scale Scientific Calculations
- High Memory Throughput
- High Clock Frequency

